

## ABSTRACT OF THE DISCLOSURE

[0036] An optically pumped semiconductor laser device having a substrate (12) having a first main area (14) and a second main area (16), a pump laser (30) and a vertically emitting laser (40) optically pumped by the pump laser (30) being arranged on the first main area (14). The first main area (14) of the substrate (12) is patterned and has first regions (20) situated at a higher level and also second regions (18) situated at a lower level. The pump laser (30) is arranged on a region (20) situated at a higher level of the substrate (12), and the vertically emitting laser (40) is arranged above intermediate layers (50, 30') on a region (18) situated at a lower level of the substrate (12). The height difference ( $\Delta$ ) between the first (20) and second (18) regions of the substrate (12) and the layer thickness of the intermediate layers (50, 30') is chosen in such a way that the pump laser (30) and the vertically emitting laser (40) are situated at the same level. A substrate which is patterned in this way enables semiconductor layers of the pump laser and of the vertically emitting laser to be applied together in a single epitaxy step.